Min Sun

List of Publications by Year
in descending order

16 papers	2,268 citations	623734 14 h-index	996975 15 g-index
16 all docs	16 docs citations	16 times ranked	2175 citing authors

#	Article	IF	Citations
1	Degradation Mechanisms of GaNâ€Based Vertical Devices: A Review. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900750.	1.8	8
2	The 2018 GaN power electronics roadmap. Journal Physics D: Applied Physics, 2018, 51, 163001.	2.8	843
3	Materials and processing issues in vertical GaN power electronics. Materials Science in Semiconductor Processing, 2018, 78, 75-84.	4.0	112
4	Large Area 1.2 kV GaN Vertical Power FinFETs with a Record Switching Figure-of-Merit. IEEE Electron Device Letters, 2018, , 1-1.	3.9	69
5	High-Performance GaN Vertical Fin Power Transistors on Bulk GaN Substrates. IEEE Electron Device Letters, 2017, 38, 509-512.	3.9	210
6	Trench formation and corner rounding in vertical GaN power devices. Applied Physics Letters, 2017, 110, .	3.3	77
7	Reduction of on-resistance and current crowding in quasi-vertical GaN power diodes. Applied Physics Letters, 2017, 111, .	3.3	39
8	Vertical GaN Junction Barrier Schottky Rectifiers by Selective Ion Implantation. IEEE Electron Device Letters, 2017, 38, 1097-1100.	3.9	136
9	Origin and Control of OFF-State Leakage Current in GaN-on-Si Vertical Diodes. IEEE Transactions on Electron Devices, 2015, 62, 2155-2161.	3.0	185
10	GaN-on-Si Vertical Schottky and p-n Diodes. IEEE Electron Device Letters, 2014, 35, 618-620.	3.9	154
11	Electrothermal Simulation and Thermal Performance Study of GaN Vertical and Lateral Power Transistors. IEEE Transactions on Electron Devices, 2013, 60, 2224-2230.	3.0	142
12	An Etch-Stop Barrier Structure for GaN High-Electron-Mobility Transistors. IEEE Electron Device Letters, 2013, 34, 369-371.	3.9	46
13	Threshold voltage control by gate oxide thickness in fluorinated GaN metal-oxide-semiconductor high-electron-mobility transistors. Applied Physics Letters, 2013, 103, .	3.3	88
14	Wafer-Level Heterogeneous Integration of GaN HEMTs and Si (100) MOSFETs. IEEE Electron Device Letters, 2012, 33, 200-202.	3.9	42
15	3000-V 4.3-$hbox{m}Omega cdot hbox{cm}^{2}$ InAlN/GaN MOSHEMTs With AlGaN Back Barrier. IEEE Electron Device Letters, 2012, 33, 982-984.	3.9	114
16	Integration of a phase change material for junction-level cooling in GaN devices. , 2012, , .		3